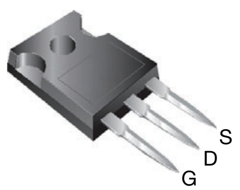
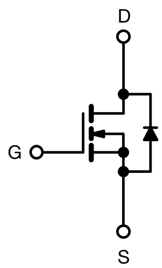
EF Series Power MOSFET With Fast Body Diode

TO-247AC





N-Channel MOSFET

PRODUCT SUMMARY		
V_{DS} (V) at T_J max.	650	
$R_{DS(on)}$ typ. (Ω) at 25 °C	V_{GS} = 10 V	0.0355
Q_g max. (nC)	410	
Q_{gs} (nC)	38	
Q_{gd} (nC)	99	
Configuration	Single	

FEATURES

- Fast body diode MOSFET using E series technology
- Reduced t_{rr}, Q_{rr}, and I_{RRM}
- Low figure-of-merit (FOM) R_{on} x Q_g
- Low switching losses due to reduced Q_{rr}
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Pb-free
RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

- Telecommunications
  - Server and telecom power supplies
- Lighting
  - High-intensity lighting (HID)
  - Light emitting diodes (LEDs)
- Consumer and computing
  - ATX power supplies
- Industrial
  - Welding
  - Battery chargers
- Renewable energy
  - Solar (PV inverters)
- Switching mode power supplies (SMPS)
- Applications using the following topologies
  - LLC
  - Phase shifted bridge (ZVS)
  - 3-level inverter
  - AC/DC bridge

ORDERING INFORMATION	
Package	TO-247AC
Lead (Pb)-free and halogen-free	SiHG70N60AEF-GE3

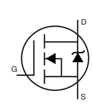
ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V_{DS}	600	V
Gate-source voltage			V_{GS}	± 20	
Gate-source voltage AC (f > 1 Hz)				30	
Continuous drain current (T_J = 150 °C)	V_{GS} at 10 V	T_C = 25 °C	I_D	60	A
		T_C = 100 °C		38	
Pulsed drain current [a]			I_{DM}	173	
Linear derating factor				3.3	W/°C
Single pulse avalanche energy [b]			E_{AS}	1019	mJ
Maximum power dissipation			P_D	417	W
Operating junction and storage temperature range			T_J, T_{stg}	-55 to +150	°C
Drain-source voltage slope	T_J = 125 °C		dv/dt	70	V/ns
Reverse diode dv/dt [d]				50	
Soldering recommendations (peak temperature) [c]	For 10 s			300	°C

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature
b. V_{DD} = 140 V, starting T_J = 25 °C, L = 28.2 mH, R_g = 25 Ω, I_{AS} = 8.5 A
c. 1.6 mm from case
d. I_{SD} = 35 A, di/dt = 300 A/μs, V_{DS} = 400 V

THERMAL RESISTANCE RATINGS				
PARAMETER	**SYMBOL**	**TYP.**	**MAX.**	**UNIT**
Maximum junction-to-ambient	R_{thJA}	-	40	°C/W
Maximum junction-to-case (drain)	R_{thJC}	-	0.3	

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 μA		600	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 1 mA		-	0.62	-	V/°C
Gate-source threshold voltage (N)	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA		2	-	4	V
Gate-source leakage	I_{GSS}	V_{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} = 480 V, V_{GS} = 0 V		-	-	1	μA
		V_{DS} = 480 V, V_{GS} = 0 V, T_J = 125 °C		-	-	2	mA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 35 A	-	0.0355	0.041	Ω
Forward transconductance [a]	g_{fs}	V_{DS} = 30 V, I_D = 35 A		-	23	-	S
Dynamic							
Input capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 100 V, f = 1 MHz		-	5348	-	pF
Output capacitance	C_{oss}			-	238	-	
Reverse transfer capacitance	C_{rss}			-	7	-	
Effective output capacitance, energy related [a]	$C_{o(er)}$	V_{DS} = 0 V to 480 V, V_{GS} = 0 V		-	159	-	
Effective output capacitance, time related [b]	$C_{o(tr)}$			-	810	-	
Total gate charge	Q_g	V_{GS} = 10 V	I_D = 35 A, V_{DS} = 480 V	-	205	410	nC
Gate-source charge	Q_{gs}			-	38	-	
Gate-drain charge	Q_{gd}			-	99	-	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 480 V, I_D = 35 A, V_{GS} = 10 V, R_g = 9.1 Ω		-	45	90	ns
Rise time	t_r			-	104	208	
Turn-off delay time	$t_{d(off)}$			-	219	438	
Fall time	t_f			-	113	226	
Gate input resistance	R_g	f = 1 MHz, open drain		0.5	1.0	2.0	Ω
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	60	A
Pulsed diode forward current	I_{SM}			-	-	173	
Diode forward voltage	V_{SD}	T_J = 25 °C, I_S = 35 A, V_{GS} = 0 V		-	0.9	1.2	V
Reverse recovery time	t_{rr}	T_J = 25 °C, I_F = I_S = 35 A, di/dt = 100 A/μs, V_R = 400 V		-	184	368	ns
Reverse recovery charge	Q_{rr}			-	1.6	3.2	μC
Reverse recovery current	I_{RRM}			-	16	-	A

Notes

a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}

b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

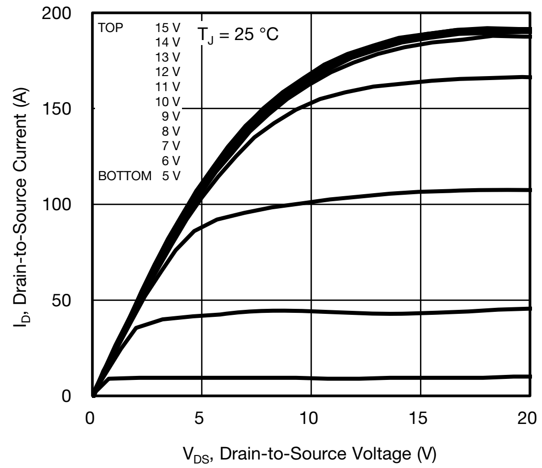


Fig. 1 - Typical Output Characteristics

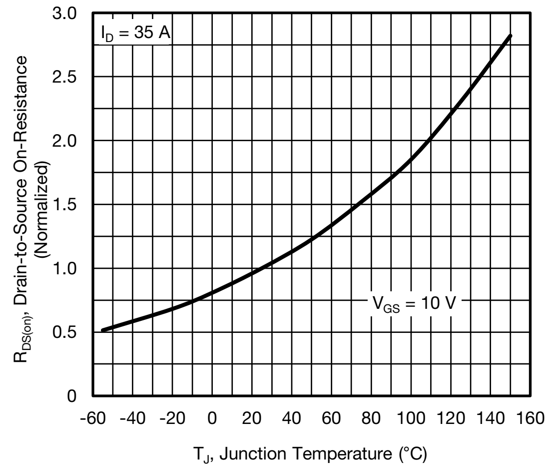


Fig. 4 - Normalized On-Resistance vs. Temperature

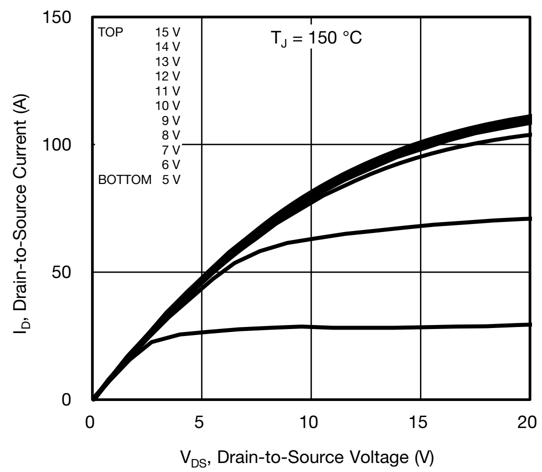


Fig. 2 - Typical Output Characteristics

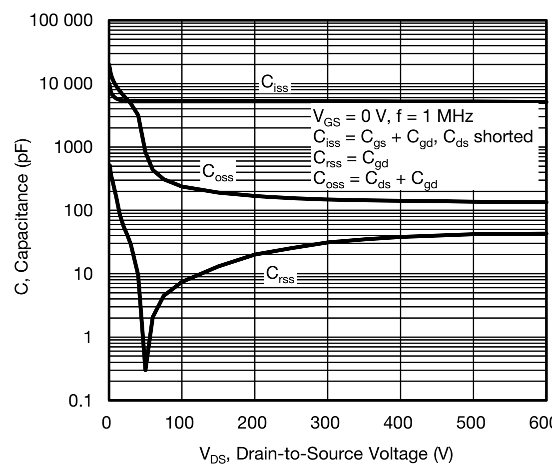


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

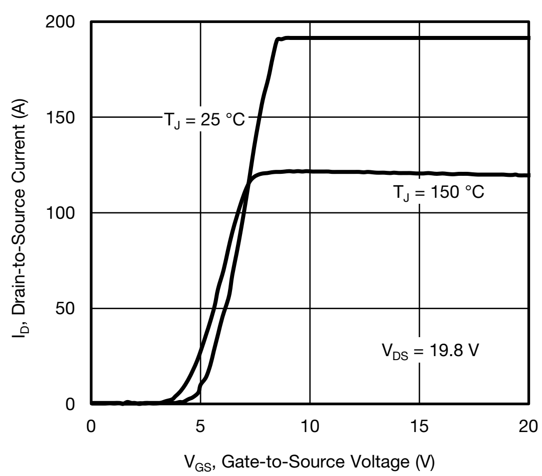


Fig. 3 - Typical Transfer Characteristics

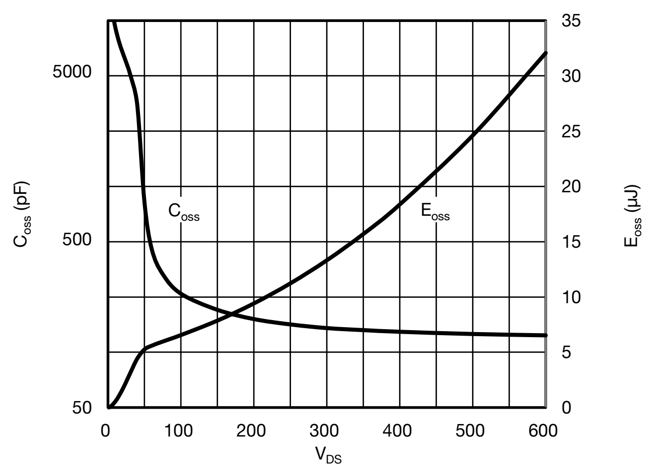


Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}

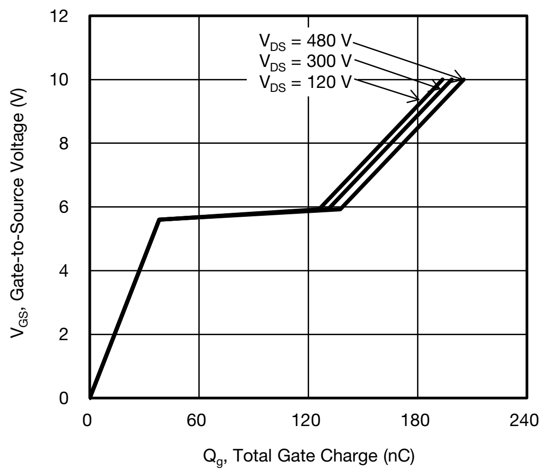


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

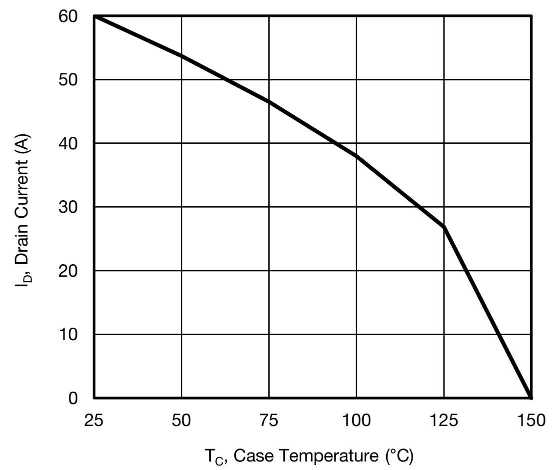


Fig. 10 - Maximum Drain Current vs. Case Temperature

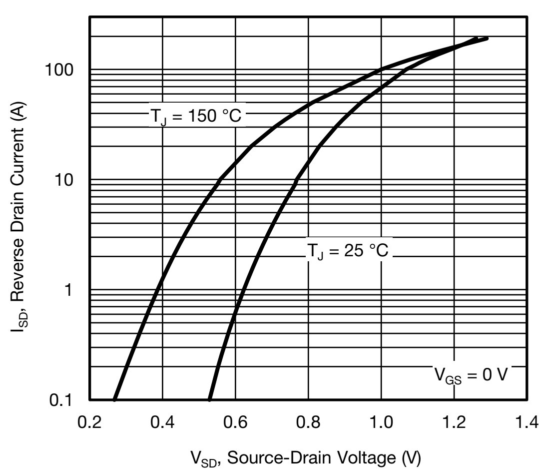


Fig. 8 - Typical Source-Drain Diode Forward Voltage

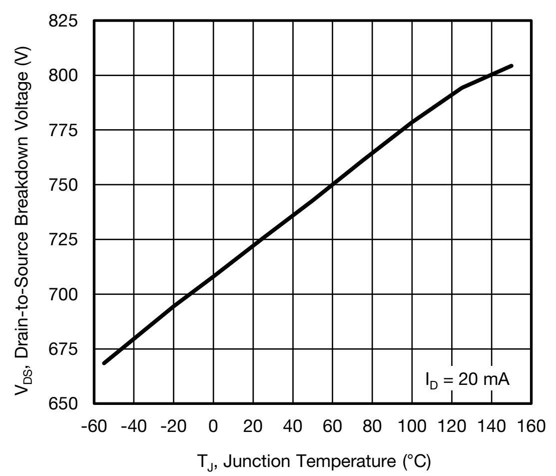
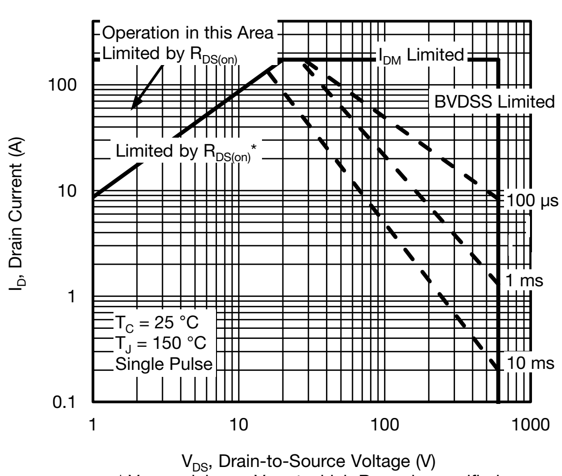


Fig. 11 - Temperature vs. Drain-to-Source Voltage



* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Fig. 9 - Maximum Safe Operating Area

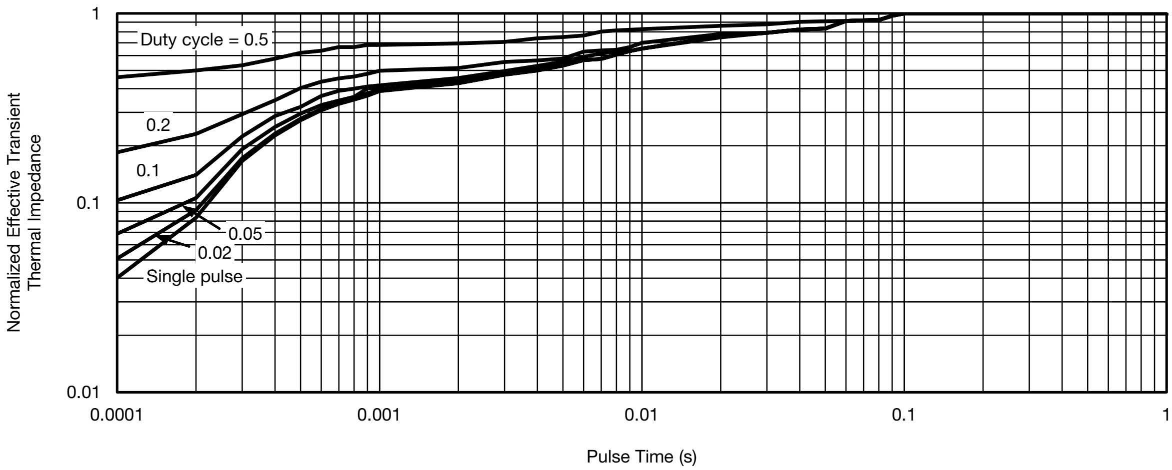


Fig. 12 - Normalized Transient Thermal Impedance, Junction-to-Case

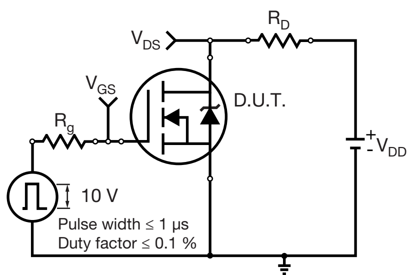


Fig. 13 - Switching Time Test Circuit

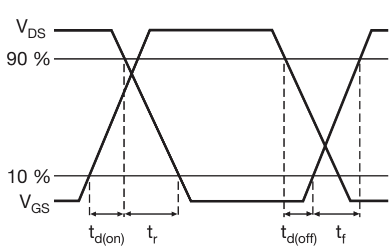


Fig. 14 - Switching Time Waveforms

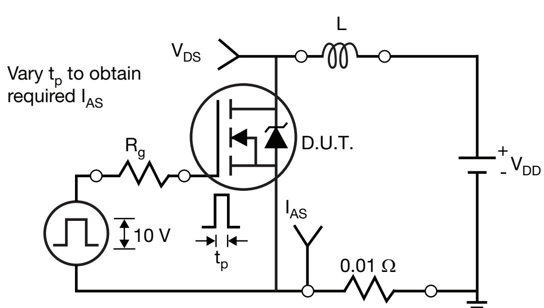


Fig. 15 - Unclamped Inductive Test Circuit

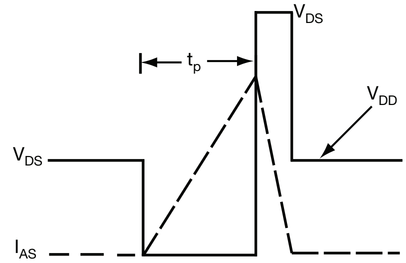


Fig. 16 - Unclamped Inductive Waveforms

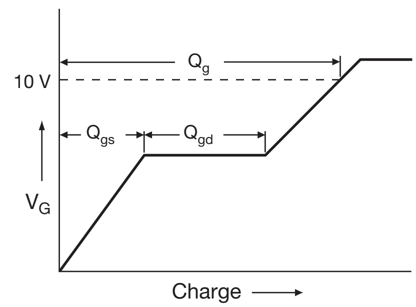


Fig. 17 - Basic Gate Charge Waveform

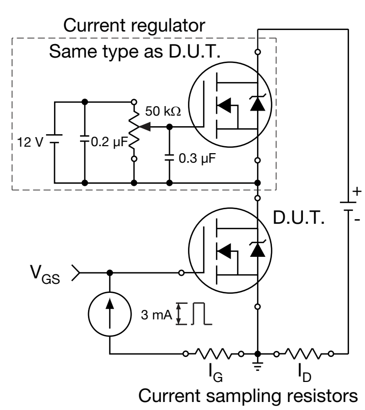
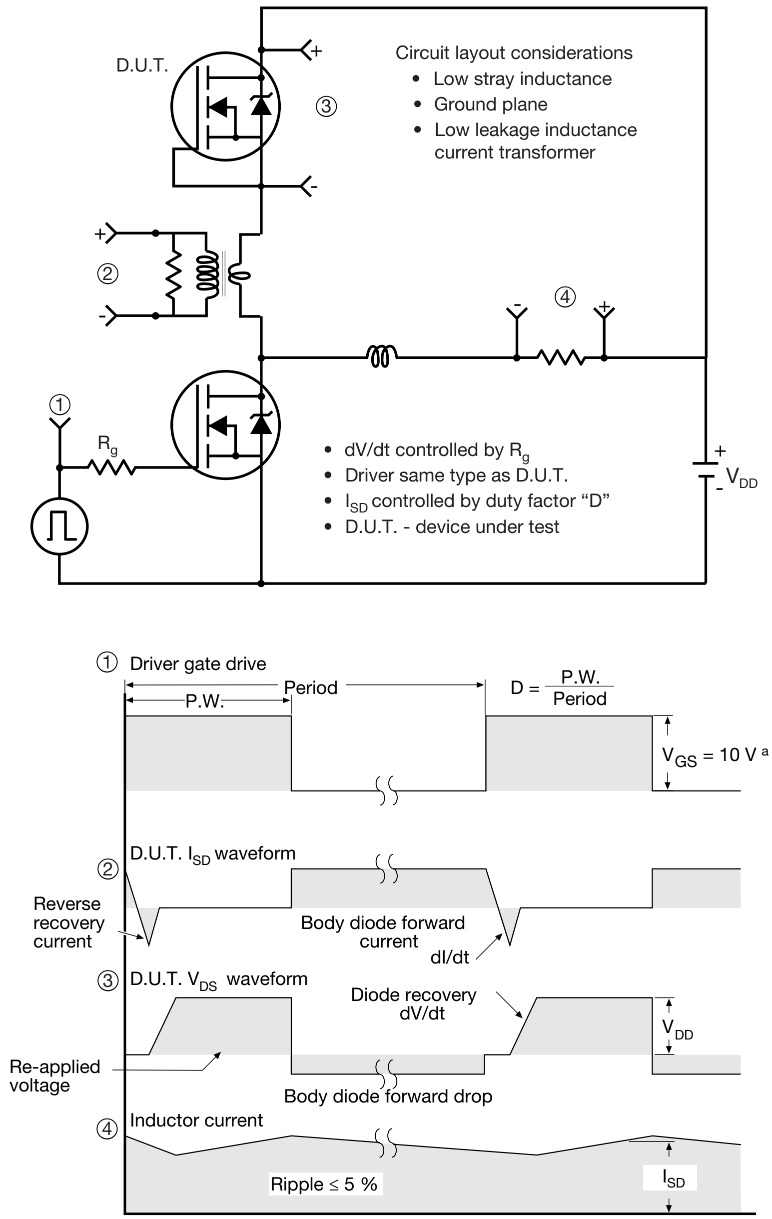


Fig. 18 - Gate Charge Test Circuit

For technical questions, contact: hvm@vishay.com

Peak Diode Recovery dV/dt Test Circuit



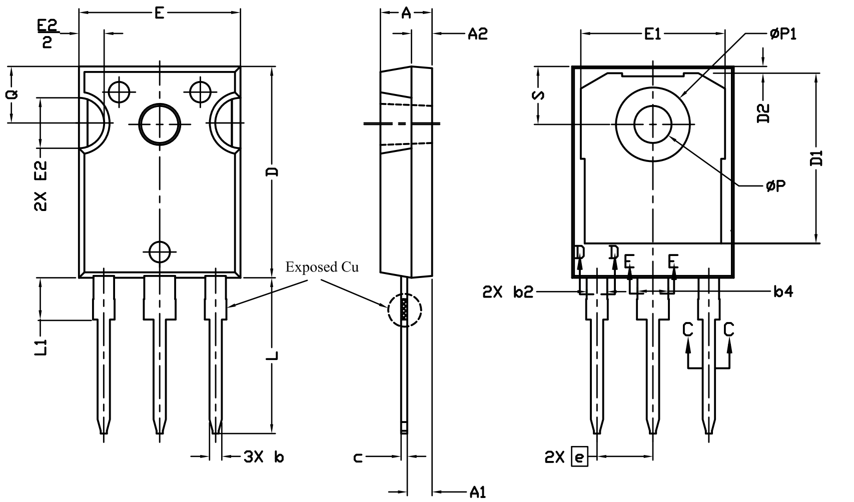
Note

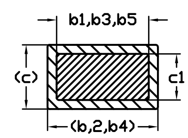
a. V_{GS} = 5 V for logic level devices

Fig. 19 - For N-Channel

TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9





Section C--C, D--D, E--E

	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
A	4.83	5.21	
A1	2.29	2.55	
A2	1.50	2.49	
b	1.12	1.33	
b1	1.12	1.28	
b2	1.91	2.39	6
b3	1.91	2.34	
b4	2.87	3.22	6, 8
b5	2.87	3.18	
c	0.55	0.69	6
c1	0.55	0.65	
D	20.40	20.70	4

	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
D1	16.25	16.85	5
D2	0.56	0.76	
E	15.50	15.87	4
E1	13.46	14.16	5
E2	4.52	5.49	3
e	5.44 BSC		
L	14.90	15.40	
L1	3.96	4.16	6
Ø P	3.56	3.65	7
Ø P1	7.19 ref.		
Q	5.31	5.69	
S	5.54	5.74	

Notes

(1) Package reference: JEDEC® TO247, variation AC

(2) All dimensions are in mm

(3) Slot required, notch may be rounded

(4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body

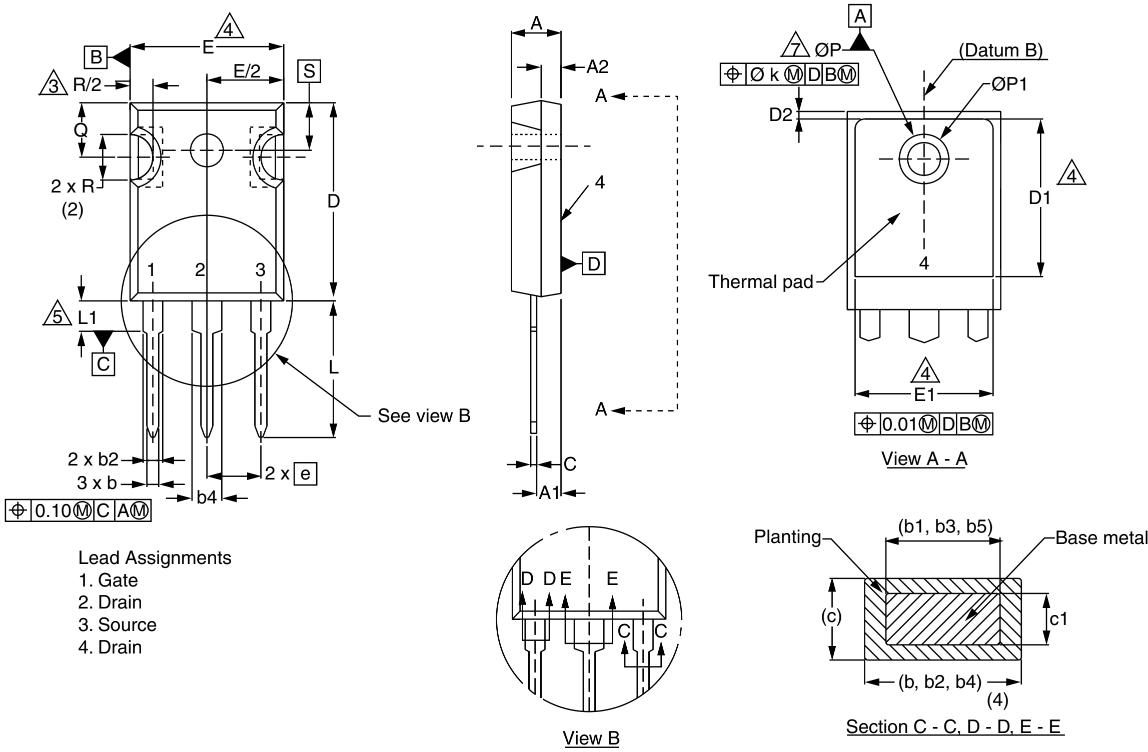
(5) Thermal pad contour optional with dimensions D1 and E1

(6) Lead finish uncontrolled in L1

(7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm

(8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition

VERSION 2: FACILITY CODE = Y



	MILLIMETERS					MILLIMETERS		
DIM.	**MIN.**	**MAX.**	**NOTES**		**DIM.**	**MIN.**	**MAX.**	**NOTES**
A	4.58	5.31			D2	0.51	1.30	
A1	2.21	2.59			E	15.29	15.87	
A2	1.17	2.49			E1	13.72	-	
b	0.99	1.40			e	5.46 BSC		
b1	0.99	1.35			Ø k	0.254		
b2	1.53	2.39			L	14.20	16.25	
b3	1.65	2.37			L1	3.71	4.29	
b4	2.42	3.43			Ø P	3.51	3.66	
b5	2.59	3.38			Ø P1	-	7.39	
c	0.38	0.86			Q	5.31	5.69	
c1	0.38	0.76			R	4.52	5.49	
D	19.71	20.82			S	5.51 BSC		
D1	13.08	-						
ECN: E19-0614-Rev. E, 08-Jan-2020 DWG: 5971								

Notes

(1) Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

(4) Thermal pad contour optional with dimensions D1 and E1

(5) Lead finish uncontrolled in L1

(6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

(7) Outline conforms to JEDEC outline TO-247 with exception of dimension c

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